Gate-Defined Quantum Confinement in InSe-Based van

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Citation Report

#	Article	IF	Citations
1	High Mobilities in Layered InSe Transistors with Indiumâ€Encapsulationâ€Induced Surface Charge Doping. Advanced Materials, 2018, 30, e1803690.	11.1	101
2	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. 2D Materials, 2018, 5, 035040.	2.0	7
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5	Gate defined quantum dot realized in a single crystalline InSb nanosheet. Applied Physics Letters, 2019, 114, .	1.5	12
6	Indirect to Direct Gap Crossover in Two-Dimensional InSe Revealed by Angle-Resolved Photoemission Spectroscopy. ACS Nano, 2019, 13, 2136-2142.	7.3	63
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9	Recent Advances in Quantum Effects of 2D Materials. Advanced Quantum Technologies, 2019, 2, 1800111.	1.8	32
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16	The optical properties of few-layer InSe. Journal of Applied Physics, 2020, 128, .	1.1	23
17	Large-area optoelectronic-grade InSe thin films via controlled phase evolution. Applied Physics Reviews, 2020, 7, .	5.5	17
18	Realizing Optoelectronic Devices from Crumpled Two-Dimensional Material Heterostructures. ACS Applied Materials & Interfaces, 2020, 12, 48910-48916.	4.0	13

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20	Oxidation-boosted charge trapping in ultra-sensitive van der Waals materials for artificial synaptic features. Nature Communications, 2020, 11, 2972.	5.8	83
21	Enhanced Optical Emission from 2D InSe Bent onto Siâ€Pillars. Advanced Optical Materials, 2020, 8, 2000828.	3.6	17
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